WHAT IS CLAIMED IS:

- 1. A semiconductor device comprising:
 - a semiconductor substrate;
- a diffusion structure formed on the semiconductor substrate;
 - a trench formed in the diffusion structure; and
- a semiconductor component separated and isolated from surrounding areas thereof in the substrate by the trench, wherein the trench defines a size of the semiconductor component.
- 2. The semiconductor device according to claim 1, further comprising:
- a plurality of trenches formed in the diffusion structure; and
- a plurality of semiconductor components of a kind separated and isolated from surrounding areas thereof in the substrate by the trenches, wherein the trenches define sizes of the semiconductor components.
- 3. The semiconductor device according to claim 1, wherein the semiconductor substrate is a silicon on insulator substrate.
- 4. The semiconductor device according to claim 3, wherein: the silicon on insulator substrate includes an insulating layer and a semiconductor layer;

the semiconductor layer is formed on the insulating layer; and

the semiconductor layer has a thickness equal to or less than five micrometers.

- 5. The semiconductor device according to claim 1, wherein the trench is filled in with borophosphosilicate glass.
- 6. The semiconductor device according to claim 1, wherein the diffusion structure includes a repeated pattern.
- 7. The semiconductor device according to claim 1, wherein the diffusion structure includes diffusion regions in rectangular shape arranged in a repeated pattern.
- 8. The semiconductor device according to claim 1, wherein the semiconductor component is an analog component for processing an analog signal.
- 9. The semiconductor device according to claim 8, wherein the analog component is a bipolar transistor.
- 10. The semiconductor device according to claim 1, wherein the semiconductor device is a power component for controlling power supply.
- 11. The semiconductor device according to claim 10, wherein

the power component is a laterally diffused metal oxide semiconductor transistor.

- 12. The semiconductor device according to claim 10, wherein the power component is an insulated gate bipolar transistor.
- 13. The semiconductor device according to claim 1, wherein the semiconductor device is a hybrid-IC in which different kinds of semiconductors are integrated in a single chip.
- 14. A method for manufacturing a semiconductor device that includes a semiconductor component formed on a substrate, comprising:

forming a diffusion structure larger than the semiconductor component in a region of the substrate in which the semiconductor component is formed;

separating a part of the diffusion structure from a surrounding area thereof by the trench to form the semiconductor component along with defining a size of the semiconductor component; and

connecting a metallization pattern to the semiconductor component.

15. The method according to claim 14, wherein the semiconductor substrate, in a region of which the diffusion structure is formed, is a silicon on insulator substrate.

16. The method according to claim 15, wherein:

the silicon on insulator substrate includes a semiconductor layer formed on an insulating layer; and

the semiconductor layer is equal to or less than five micrometers.

- 17. The method according to claim 14 further comprising filling in the trench with borophosphosilicate glass.
- 18. The method according to claim 14, wherein the diffusion structure is formed including a repeated pattern in the region.
- 19. The method according to claim 14, wherein the diffusion structure is formed including diffusion regions shaped in a rectangular.
- 20. The method according to claim 14, wherein the semiconductor device formed in separating step is an analog component for processing an analog signal.
- 21. The method according to claim 20, wherein the analog component is a bipolar transistor.
- 22. The method according to claim 14, wherein the semiconductor device formed in separating step is a power component for controlling power supply.

- 23. The method according to claim 22, wherein the power component is an insulated gate bipolar transistor.
- 24. The method according to claim 22, wherein the power component is a laterally diffused metal oxide semiconductor transistor.
- 25. The method according to claim 14, wherein the semiconductor device manufactured by the method is a hybrid IC including different kinds of semiconductor components integrated into a single chip.
- 26. A method for manufacturing a semiconductor device that includes a plurality of semiconductor components of a kind in a region of a semiconductor substrate, comprising:

forming a common diffusion structure in the region in which the semiconductor components are formed;

separating parts of the diffusion structure from a surrounding area thereof by trenches to form the semiconductor components along with defining sizes of the semiconductor components; and

connecting metallization patterns to the semiconductor components.

27. The method according to claim 26, wherein the semiconductor substrate, in a region of which the diffusion structure is formed, is a silicon on insulator substrate.

28. The method according to claim 27, wherein:

the silicon on insulator substrate includes a semiconductor layer formed on an insulating layer; and

the semiconductor layer is equal to or less than five micrometers.

- 29. The method according to claim 26, further comprising filling in the trench with borophosphosilicate glass.
- 30. The method according to claim 26, wherein the diffusion structure is formed including a repeated pattern in the region.
- 31. The method according to claim 26, wherein the diffusion structure is formed including diffusion regions shaped in a rectangular.
- 32. The method according to claim 26, wherein the semiconductor device formed in separating step is an analog component for processing an analog signal.
- 33. The method according to claim 32, wherein the analog component is a bipolar transistor.
- 34. The method according to claim 26, wherein the semiconductor device formed in separating step is a power component for controlling power supply.

- 35. The method according to claim 34, wherein the power component is an insulated gate bipolar transistor.
- 36. The method according to claim 34, wherein the power component is a laterally diffused metal oxide semiconductor transistor.
- 37. The method according to claim 26, wherein the semiconductor device manufactured by the method is a hybrid IC including different kinds of semiconductor components integrated into a single chip.